

Seung-Geun Kim

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Enhancement of Synaptic Characteristics Achieved by the Optimization of Proton-Electron Coupling Effect in a Solid-State Electrolyte-Gated Transistor. <i>Small</i> , 2021, 17, e2100242.	10.0	13
2	Analysis of the Thermal Degradation Effect on a HfO ₂ -Based Memristor Synapse Caused by Oxygen Affinity of a Top Electrode Metal and on a Neuromorphic System. <i>ACS Applied Electronic Materials</i> , 2021, 3, 5584-5591.	4.3	8
3	Hysteresis Modulation on Van der Waals-Based Ferroelectric Field-Effect Transistor by Interfacial Passivation Technique and Its Application in Optic Neural Networks. <i>Small</i> , 2020, 16, e2004371.	10.0	35
4	Ultralow Schottky Barrier Height Achieved by Using Molybdenum Disulfide/Dielectric Stack for Source/Drain Contact. <i>ACS Applied Materials & Interfaces</i> , 2019, 11, 34084-34090.	8.0	6
5	Infrared Detectable MoS ₂ Phototransistor and Its Application to Artificial Multilevel Optic-Neural Synapse. <i>ACS Nano</i> , 2019, 13, 10294-10300.	14.6	96
6	Schottky Barrier Height Modulation Using Interface Characteristics of MoS ₂ Interlayer for Contact Structure. <i>ACS Applied Materials & Interfaces</i> , 2019, 11, 6230-6237.	8.0	19
7	Reduction of Threshold Voltage Hysteresis of MoS ₂ Transistors with 3-Aminopropyltriethoxysilane Passivation and Its Application for Improved Synaptic Behavior. <i>ACS Applied Materials & Interfaces</i> , 2019, 11, 20949-20955.	8.0	19
8	Super steep-switching (SS \approx 2 mV/decade) phase-FinFET with Pb(Zr _{0.52} Ti _{0.48})O ₃ threshold switching device. <i>Applied Physics Letters</i> , 2018, 113, .	3.3	8
9	An Electrical Analysis of a Metal-Interlayer-Semiconductor Structure on High-Quality Si ^x Ge ^{1-x} Films for Non-Alloyed Ohmic Contact. <i>Journal of Nanoscience and Nanotechnology</i> , 2017, 17, 7323-7326.	0.9	0